



**FEATURES**

Dimensions are in inch [metric] units.

- Ideal for electron detection
- Circular active area
- 100% internal QE

**ELECTRO-OPTICAL CHARACTERISTICS AT 25°C (PER ELEMENT)**

PARAMETERS	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Active Area			15		mm <sup>2</sup>
Responsivity, $\mathcal{R}$	(see graphs on the next page)	0.07	0.08	0.09	A/W
Shunt Resistance, $R_{sH}$	$V_R = \pm 10mV$	10			MOhms
Reverse Breakdown Voltage, $V_R$	$I_R = 1\mu A$	5			Volts
Capacitance, C	$V_R = 0V$		1.5		nF
Rise Time	$V_R = 2V, R_L = 50\Omega$			2	usec

**THERMAL PARAMETERS**

STORAGE AND OPERATING TEMPERATURE RANGE	
Ambient <sup>1</sup>	-10° TO 40°C <sup>1</sup>
Nitrogen or Vacuum	-20°C TO 80°C
Maximum Junction Temperature	70°C
Lead soldering temperature <sup>2</sup>	260°C

<sup>1</sup>Temperatures exceeding these parameters may create oxide growth on the active area. Over time responsivity to low energy radiation and wavelengths below 150nm will be compromised.

<sup>2</sup>0.080" from case for 10 seconds.

Shipped with temporary cover to protect photodiode and wire bond.  
Review Opto Diode "Handling Precautions for IRD Detectors" prior to removing cover.



750 Mitchell Road, Newbury Park, California 91320  
Phone: (805) 499-0335, Fax: (805) 499-8108  
Email: sales@optodiode.com, Website: www.optodiode.com

